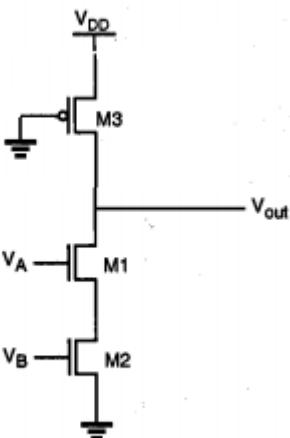


<b>Q1.</b>	<b>Choose the correct option for following questions. All the Questions are compulsory and carry equal marks</b>
1.	Power dissipation, after applying constant field scaling Option A: decreases by factor of S Option B: increases by factor of $S^3$ Option C: increases by factor of S Option D: decreases by factor of $S^2$
2.	In case of CMOS Inverter, Critical Voltage $V_{IL}$ is given by Option A: $V_{IL} = \frac{2V_{out} + V_{T0,p} - V_{DD/2} + K_R V_{T0,n}}{1+K_n}$ Option B: $V_{IL} = \frac{2V_{out} + V_{T0,p} - V_{DD} + K_R V_{T0,p}}{1 + K_R}$ Option C: $V_{IL} = \frac{2V_{out} + V_{T0,p} - V_{DD} + K_R V_{T0,n}}{1+K_R}$ Option D: $V_{IL} = \frac{2V_{out} + V_{T0,n} - V_{DD} + K_R V_{T0,p}}{1+K_R}$
3.	Consider a CMOS Inverter circuit with the following parameters: $V_{DD} = 3.3\text{ V}$ , $V_{T0,n} = 0.6\text{ V}$ , $V_{T0,p} = -0.7\text{ V}$ $K_n = 200\text{ }\mu\text{A/V}^2$ , $K_p = 80\text{ }\mu\text{A/V}^2$ Calculate $V_{IH}$ Option A: 1.08 V Option B: 1.55 V Option C: 3.3 V Option D: 0 V
4.	Identify type of Circuit 

Option A:	2 input pseudo nmos NOR gate
Option B:	2 input pseudo nmos NAND gate
Option C:	2 input CMOS OR gate
Option D:	2 input CMOS AND gate
5.	What are the limitations of Dynamic CMOS logic?
Option A:	charge latching
Option B:	charge leakage and sharing
Option C:	charge distribution
Option D:	leakage current
6.	How many TGs are required for Implementation of XOR gate? (TG means Transmission Gates)
Option A:	2
Option B:	8
Option C:	7
Option D:	4
7.	Static CMOS logic is an -----.
Option A:	ratioed logic
Option B:	non-ratioed logic
Option C:	negative logic
Option D:	positive logic
8.	Sense amplifier is used to-----.
Option A:	sense small voltage difference at bit-line
Option B:	sense bit-line capacitance
Option C:	sense impedance of bit-line
Option D:	sense resistance of bit-line
9.	In a 1T DRAM, information is stored in-----.
Option A:	latch
Option B:	parasitic capacitor
Option C:	trench capacitor
Option D:	virtual capacitor
10.	----- are designed to overcome the latency introduced by the rippling effect of the carry bits.
Option A:	Ripple carry adders
Option B:	Carry look-ahead (CLA) adders
Option C:	Ripple carry and sum look-ahead adders
Option D:	Half and full adders

<b>Q2.</b> <b>(20 Marks Each)</b>	<b>Solve any Two Questions out of Three 10 marks each</b>
A	<i>Write a note on MOSFET Capacitances.</i>
B	<i>Derive the expression of all critical voltages for CMOS inverter.</i>
C	<i>Explain interconnect scaling and crosstalk.</i>
<b>Q3.</b> <b>(20 Marks Each)</b>	<b>Solve any Two Questions out of Three 10 marks each</b>
A	<i>Explain Dynamic and Domino logic used for MOS circuit design.</i>
B	<i>Implement 4:1MUX using pass transistor and Transmission gates.</i>
C	<i>Explain working of JK flipflop using static CMOS design logic.</i>
<b>Q4.</b> <b>(20 Marks Each)</b>	<b>Solve any Two Questions out of Three 10 marks each</b>
A	<i>What is Carry select adder? Explain it's working.</i>
B	<i>Write a note on array multiplier.</i>
C	<i>What is SRAM? Explain the stability of 6T SRAM cell.</i>